



3.3-V / 5-V HIGH-SPEED DIGITAL ISOLATORS

 Check for Samples: [ISO721-Q1](#), [ISO722-Q1](#)

FEATURES

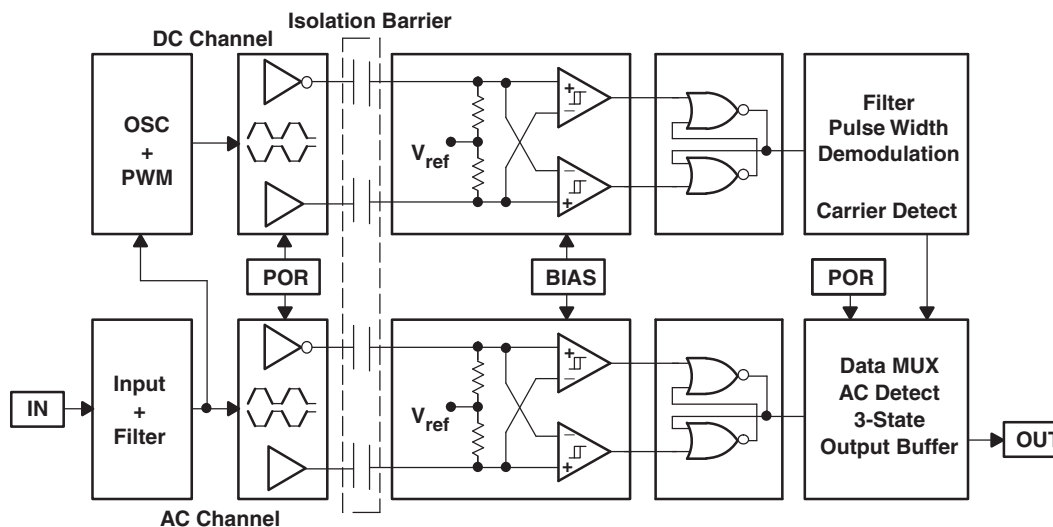
- Qualified for Automotive Applications
- 4000-V_(peak) Isolation
 - UL 1577, IEC 60747-5-2 (VDE 0884, Rev 2), IEC 61010-1
 - 50-kV/s Transient Immunity (Typ)
- Signaling Rate 0 Mbps to 150 Mbps
 - Low Propagation Delay
 - Low Pulse Skew (Pulse-Width Distortion)
- Low-Power Sleep Mode
- High Electromagnetic Immunity
- Low Input Current Requirement
- Failsafe Output
- Drop-In Replacement for Most Optical and Magnetic Isolators

DESCRIPTION

The ISO72x-Q1 is a digital isolator with a logic input and output buffer separated by a silicon oxide (SiO₂) insulation barrier. This barrier provides galvanic isolation of up to 4000 V. Used in conjunction with isolated power supplies, this device prevents noise currents on a data bus or other circuits from entering the local ground, and interfering with or damaging sensitive circuitry.

A binary input signal is conditioned, translated to a balanced signal, then differentiated by the capacitive isolation barrier. Across the isolation barrier, a differential comparator receives the logic transition information, then sets or resets a flip-flop and the output circuit accordingly. A periodic update pulse is sent across the barrier to ensure the proper dc level of the output. If this dc refresh pulse is not received for more than 4 μs, the input is assumed to be unpowered or not being actively driven, and the failsafe circuit drives the output to a logic high state.

FUNCTION DIAGRAM



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

DESCRIPTION (CONTINUED)

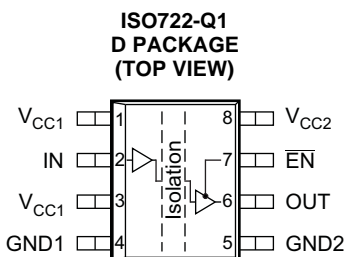
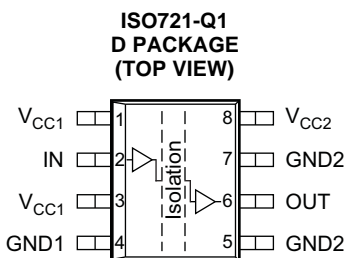
The symmetry of the dielectric and capacitor within the integrated circuitry provides for close capacitive matching and allows fast transient voltage changes between the input and output grounds without corrupting the output. The small capacitance and resulting time constant provide for fast operation with signaling rates⁽¹⁾ from 0 Mbps (dc) to 100 Mbps.

The device requires two supply voltages of 3.3 V, 5 V, or any combination. All inputs are 5-V tolerant when supplied from a 3.3-V supply, and all outputs are 4-mA CMOS. The device has a TTL input threshold and a noise-filter at the input that prevents transient pulses of up to 2 ns in duration from being passed to the output of the device.

The ISO722 device includes an active-low output enable that when driven to a high logic level, places the output in a high-impedance state and turn off internal bias circuitry to conserve power.

The ISO72x-Q1 is characterized for operation over the ambient temperature range of –40°C to 125°C.

(1) The signaling rate of a line is the number of voltage transitions that are made per second expressed in the units bps (bits per second).



ORDERING INFORMATION⁽¹⁾

T _A	PACKAGE ⁽²⁾		ORDERABLE PART NUMBER	TOP-SIDE MARKING
	–40°C to 125°C	SOIC – D	Reel of 2500	ISO721QDRQ1
ISO722QDRQ1				IS722Q

- (1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.
- (2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

Table 1. REGULATORY INFORMATION

VDE	CSA	UL
Certified according to IEC 60747-5-2	Approved under CSA Component Acceptance Notice: CA-5A	Recognized under 1577 Component Recognition Program ⁽¹⁾
File Number: 40016131	File Number: 1698195	File Number: E181974

(1) Production tested ≥ 3000 V_{RMS} for 1 second in accordance with UL 1577.

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

V_{CC}	Supply voltage ⁽²⁾ , V_{CC1} , V_{CC2}		–0.5 V to 6 V
V_I	Voltage at IN or OUT terminal		–0.5 V to 6 V
I_O	Output current		±15 mA
T_J	Maximum virtual-junction temperature		170°C
ESD	Electrostatic discharge rating	Human-Body Model ⁽³⁾	±2 kV
		Charged-Device Model ⁽⁴⁾	±1 kV

- (1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values except differential I/O bus voltages are with respect to network ground terminal and are peak voltage values. Vrms values are not listed in this publication.
- (3) JEDEC Standard 22, Test Method A114-C.01
- (4) JEDEC Standard 22, Test Method C101

RECOMMENDED OPERATING CONDITIONS

		MIN	MAX	UNIT
V_{CC}	Supply voltage ⁽¹⁾ , V_{CC1} , V_{CC2}	3	5.5	V
I_{OH}	High-level output current		4	mA
I_{OL}	Low-level output current	–4		mA
t_{ui}	Input pulse width	10		ns
V_{IH}	High-level input voltage (IN)	2	V_{CC}	V
V_{IL}	Low-level input voltage (IN)	0	0.8	V
T_A	Operating free-air temperature	–40	125	°C
T_J	Operating virtual-junction temperature	See the Thermal Characteristics table		150
H	External magnetic field intensity per IEC 61000-4-8 and IEC 61000-4-9 certification		1000	A/m

- (1) For 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V. For 3.3-V operation, V_{CC1} or V_{CC2} is specified from 3 V to 3.6 V.

IEC 60747-5-2 INSULATION CHARACTERISTICS⁽¹⁾

over recommended operating conditions (unless otherwise noted)

PARAMETER	TEST CONDITIONS	SPECIFICATIONS	UNIT
V_{IORM}	Maximum working insulation voltage	560	V
V_{PR}	Input to output test voltage	After Input/Output Safety Test Subgroup 2/3 $V_{PR} = V_{IORM} \times 1.2$, $t = 10$ s, Partial discharge < 5 pC	672
		Method a, $V_{PR} = V_{IORM} \times 1.6$, Type and sample test with $t = 10$ s, Partial discharge < 5 pC	896
		Method b1, $V_{PR} = V_{IORM} \times 1.875$, 100 % Production test with $t = 1$ s, Partial discharge < 5 pC	1050
V_{IOTM}	Transient overvoltage	$t = 60$ s	4000
R_S	Insulation resistance	$V_{IO} = 500$ V at T_S	>10 ⁹
	Pollution degree		2

- (1) Climatic Classification 40/125/21

ELECTRICAL CHARACTERISTICS: V_{CC1} and V_{CC2} 5-V⁽¹⁾ OPERATION

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT		
I_{CC1}	V_{CC1} supply current	Quiescent	$V_I = V_{CC}$ or 0 V, No load		0.5	1	mA		
		25 Mbps			2	4			
I_{CC2}	V_{CC2} supply current	ISO722-Q1 Sleep Mode	$V_I = V_{CC}$ or 0 V, No load			200	μ A		
		Quiescent				\overline{EN} at 0 V or ISO721-Q1		8	12
		25 Mbps						10	14
V_{OH}	High-level output voltage		$I_{OH} = -4$ mA, See Figure 1		$V_{CC} - 0.8$	4.6	V		
			$I_{OH} = -20$ μ A, See Figure 1		$V_{CC} - 0.1$	5			
V_{OL}	Low-level output voltage		$I_{OL} = 4$ mA, See Figure 1		0.2	0.4	V		
			$I_{OL} = 20$ μ A, See Figure 1		0	0.1			
$V_{I(HYS)}$	Input voltage hysteresis				150		mV		
I_{IH}	High-level input current		IN at 2 V			10	μ A		
I_{IL}	Low-level input current		IN at 0.8 V		-10				
I_{OZ}	High-impedance output current	ISO722-Q1	\overline{EN} , IN at V_{CC}			1	μ A		
C_1	Input capacitance to ground		IN at V_{CC} , $V_I = 0.4 \sin(4E6\pi t)$		1		pF		
CMTI	Common-mode transient immunity		$V_I = V_{CC}$ or 0 V, See Figure 5		15	50	kV/ μ s		

(1) For 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V. For 3.3-V operation, V_{CC1} or V_{CC2} is specified from 3 V to 3.6 V.

SWITCHING CHARACTERISTICS: V_{CC1} and V_{CC2} 5-V OPERATION

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT	
t_{PLH}	Propagation delay, low-to-high-level output		See Figure 1		17	24	ns	
t_{PHL}	Propagation delay, high-to-low-level output		See Figure 1		17	24	ns	
$t_{sk(p)}$	Pulse skew $ t_{PHL} - t_{PLH} $		See Figure 1		0.5	2	ns	
$t_{sk(PP)}$	Part-to-part skew				0	3	ns	
t_r	Output signal rise time		See Figure 1		1		ns	
t_f	Output signal fall time		See Figure 1		1		ns	
t_{pHZ}	Sleep-mode propagation delay, high-level-to-high-impedance output	ISO722-Q1	See Figure 2		6	8	15	ns
t_{pZH}	Sleep-mode propagation delay, high-impedance-to-high-level output				3.5	4	8	μ s
t_{pLZ}	Sleep-mode propagation delay, low-level-to-high-impedance output				5.5	8	15	ns
t_{pZL}	Sleep-mode propagation delay, high-impedance-to-low-level output				See Figure 3	4	5	8
t_{fs}	Failsafe output delay time from input power loss		See Figure 4		3		μ s	
$t_{jit(PP)}$	Peak-to-peak eye-pattern jitter		100-Mbps NRZ data input, See Figure 6		2		ns	
			100-Mbps unrestricted bit run length data input, See Figure 6		3			

(1) $t_{sk(PP)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

ELECTRICAL CHARACTERISTICS: V_{CC1} at 5-V, V_{CC2} at 3.3-V⁽¹⁾ OPERATION

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT	
I_{CC1}	V_{CC1} supply current	Quiescent	$V_I = V_{CC}$ or 0 V, No load		0.5	1	mA	
		25 Mbps			2	4		
I_{CC2}	V_{CC2} supply current	ISO722-Q1	$V_I = V_{CC}$ or 0 V, No load		150		μ A	
		Quiescent			4 6.5			
		25 Mbps			5 7.5			
V_{OH}	High-level output voltage	$I_{OH} = -4$ mA, See Figure 1		$V_{CC} - 0.4$	3		V	
		$I_{OH} = -20$ μ A, See Figure 1		$V_{CC} - 0.1$	3.3			
V_{OL}	Low-level output voltage	$I_{OL} = 4$ mA, See Figure 1		0.2		0.4	V	
		$I_{OL} = 20$ μ A, See Figure 1		0		0.1		
$V_{I(HYS)}$	Input voltage hysteresis			150			mV	
I_{IH}	High-level input current	IN at 2 V				10	μ A	
I_{IL}	Low-level input current	IN at 0.8 V		-10			μ A	
I_{OZ}	High-impedance output current	ISO722-Q1	\overline{EN} , IN at V_{CC}				1	μ A
C_1	Input capacitance to ground	IN at V_{CC} , $V_I = 0.4 \sin(4E6\pi t)$				1	pF	
CMTI	Common-mode transient immunity	$V_I = V_{CC}$ or 0 V, See Figure 5		15	40		kV/ μ s	

 (1) For 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V. For 3.3-V operation, V_{CC1} or V_{CC2} is specified from 3 V to 3.6 V.

SWITCHING CHARACTERISTICS: V_{CC1} at 5-V, V_{CC2} at 3.3-V OPERATION

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay, low-to-high-level output	See Figure 1			19	30	ns
t_{PHL}	Propagation delay, high-to-low-level output	See Figure 1			19	30	ns
$t_{sk(p)}$	Pulse skew $ t_{PHL} - t_{PLH} $	See Figure 1			0.5	3	ns
$t_{sk(PP)}$	Part-to-part skew				0	5	ns
t_r	Output signal rise time	See Figure 1			2		ns
t_f	Output signal fall time	See Figure 1			2		ns
t_{pHZ}	Sleep-mode propagation delay, high-level-to-high-impedance output	ISO722-Q1	See Figure 2	7	13	25	ns
t_{pZH}	Sleep-mode propagation delay, high-impedance-to-high-level output			5	6	8	μ s
t_{pLZ}	Sleep-mode propagation delay, low-level-to-high-impedance output		See Figure 3	7	13	25	ns
t_{pZL}	Sleep-mode propagation delay, high-impedance-to-low-level output			5	6	8	μ s
t_{fs}	Failsafe output delay time from input power loss	See Figure 4			3		μ s
$t_{jit(PP)}$	Peak-to-peak eye-pattern jitter	100-Mbps NRZ data input, See Figure 6			2		ns
		100-Mbps unrestricted bit run length data input, See Figure 6			3		

 (1) $t_{sk(PP)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

ELECTRICAL CHARACTERISTICS: V_{CC1} at 3.3-V, V_{CC2} at 5-V⁽¹⁾ OPERATION

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
I_{CC1}	V_{CC1} supply current	Quiescent	$V_I = V_{CC}$ or 0 V, No load		0.3	0.5	mA
		25 Mbps			1	2	
I_{CC2}	V_{CC2} supply current	ISO722-Q1 Sleep Mode	$V_I = V_{CC}$ or 0 V, No load	\overline{EN} at V_{CC}		200	μ A
		Quiescent			\overline{EN} at 0 V or ISO721-Q1		
		25 Mbps	$V_I = V_{CC}$ or 0 V, No load			10	14
V_{OH}	High-level output voltage	$I_{OH} = -4$ mA, See Figure 1		$V_{CC} - 0.8$	4.6		V
		$I_{OH} = -20$ μ A, See Figure 1		$V_{CC} - 0.1$	5		
V_{OL}	Low-level output voltage	$I_{OL} = 4$ mA, See Figure 1			0.2	0.4	V
		$I_{OL} = 20$ μ A, See Figure 1			0	0.1	
$V_{I(HYS)}$	Input voltage hysteresis				150		mV
I_{IH}	High-level input current	IN at 2 V				10	μ A
I_{IL}	Low-level input current	IN at 0.8 V		-10			μ A
I_{OZ}	High-impedance output current	ISO722-Q1	\overline{EN} , IN at V_{CC}			1	μ A
C_1	Input capacitance to ground	IN at V_{CC} , $V_I = 0.4 \sin(4E6\pi t)$			1		pF
CMTI	Common-mode transient immunity	$V_I = V_{CC}$ or 0 V, See Figure 5		15	40		kV/ μ s

(1) For 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V. For 3.3-V operation, V_{CC1} or V_{CC2} is specified from 3 V to 3.6 V.

SWITCHING CHARACTERISTICS: V_{CC1} at 3.3-V, V_{CC2} at 5-V OPERATION

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT		
t_{PLH}	Propagation delay, low-to-high-level output	See Figure 1			17	30	ns		
t_{PHL}	Propagation delay, high-to-low-level output	See Figure 1			17	30	ns		
$t_{sk(p)}$	Pulse skew $ t_{PHL} - t_{PLH} $	See Figure 1			0.5	3	ns		
$t_{sk(pp)}$	Part-to-part skew				0	5	ns		
t_r	Output signal rise time	See Figure 1			2		ns		
t_f	Output signal fall time	See Figure 1			2		ns		
t_{pHZ}	Sleep-mode propagation delay, high-level-to-high-impedance output	ISO722-Q1	See Figure 2		7	9	15	ns	
t_{pZH}	Sleep-mode propagation delay, high-impedance-to-high-level output				4.5	5	8	μ s	
t_{pLZ}	Sleep-mode propagation delay, low-level-to-high-impedance output			See Figure 3		7	9	15	ns
t_{pZL}	Sleep-mode propagation delay, high-impedance-to-low-level output					4.5	5	8	μ s
t_{fs}	Failsafe output delay time from input power loss	See Figure 4			3		μ s		
$t_{jit(PP)}$	Peak-to-peak eye-pattern jitter	100-Mbps NRZ data input, See Figure 6			2		ns		
		100-Mbps unrestricted bit run length data input, See Figure 6			3				

(1) $t_{sk(PP)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

ELECTRICAL CHARACTERISTICS: V_{CC1} and V_{CC2} at 3.3-V⁽¹⁾ OPERATION

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
I_{CC1}	V_{CC1} supply current	Quiescent	$V_I = V_{CC}$ or 0 V, No load		0.3	0.5	mA
		25 Mbps			1	2	
I_{CC2}	V_{CC2} supply current	ISO722-Q1 Sleep Mode	$V_I = V_{CC}$ or 0 V, No load			150	μ A
				\overline{EN} at V_{CC}			
		Quiescent	\overline{EN} at 0 V or ISO721-Q1		4	6.5	mA
	25 Mbps	$V_I = V_{CC}$ or 0 V, No load		5	7.5		
V_{OH}	High-level output voltage		$I_{OH} = -4$ mA, See Figure 1	$V_{CC} - 0.4$	3		V
			$I_{OH} = -20$ μ A, See Figure 1	$V_{CC} - 0.1$	3.3		
V_{OL}	Low-level output voltage		$I_{OL} = 4$ mA, See Figure 1		0.2	0.4	V
			$I_{OL} = 20$ μ A, See Figure 1		0	0.1	
$V_{I(HYS)}$	Input voltage hysteresis				150		mV
I_{IH}	High-level input current		IN at 2 V			10	μ A
I_{IL}	Low-level input current		IN at 0.8 V	-10			μ A
I_{OZ}	High-impedance output current	ISO722-Q1	\overline{EN} , IN at V_{CC}			1	μ A
C_1	Input capacitance to ground		IN at V_{CC} , $V_I = 0.4 \sin(4E6\pi t)$		1		pF
CMTI	Common-mode transient immunity		$V_I = V_{CC}$ or 0 V, See Figure 5	15	40		kV/ μ s

 (1) For 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V. For 3.3-V operation, V_{CC1} or V_{CC2} is specified from 3 V to 3.6 V.

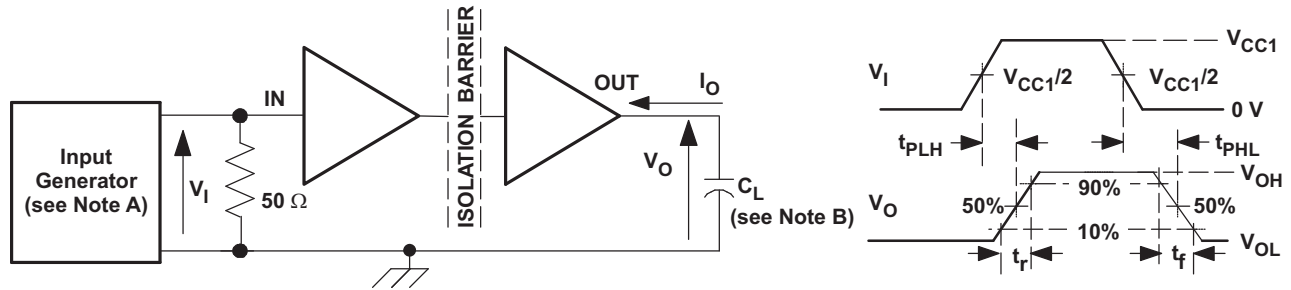
SWITCHING CHARACTERISTICS: V_{CC1} and V_{CC2} at 3.3-V OPERATION

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay, low-to-high-level output		See Figure 1		20	34	ns
t_{PHL}	Propagation delay, high-to-low-level output		See Figure 1		20	34	ns
$t_{sk(p)}$	Pulse skew $ t_{PHL} - t_{PLH} $		See Figure 1		0.5	3	ns
$t_{sk(pp)}$	Part-to-part skew				0	5	ns
t_r	Output signal rise time		See Figure 1		2		ns
t_f	Output signal fall time		See Figure 1		2		ns
t_{pHZ}	Sleep-mode propagation delay, high-level-to-high-impedance output	ISO722-Q1	See Figure 2	7	13	25	ns
t_{pZH}	Sleep-mode propagation delay, high-impedance-to-high-level output			5	6	8	μ s
t_{pLZ}	Sleep-mode propagation delay, low-level-to-high-impedance output			7	13	25	ns
t_{pZL}	Sleep-mode propagation delay, high-impedance-to-low-level output			5	6	8	μ s
t_{fs}	Failsafe output delay time from input power loss		See Figure 4		3		μ s
$t_{jit(pp)}$	Peak-to-peak eye-pattern jitter		100-Mbps NRZ data input, See Figure 6		2		ns
			100-Mbps unrestricted bit run length data input, See Figure 6		3		

 (1) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

PARAMETER MEASUREMENT INFORMATION



- A. The input pulse is supplied by a generator having the following characteristics:
 PRR ≤ 50 kHz, 50% duty cycle, $t_r \leq 3$ ns, $t_f \leq 3$ ns, $Z_O = 50 \Omega$.
- B. $C_L = 15$ pF and includes instrumentation and fixture capacitance within ±20%.

Figure 1. Switching Characteristic Test Circuit and Voltage Waveforms

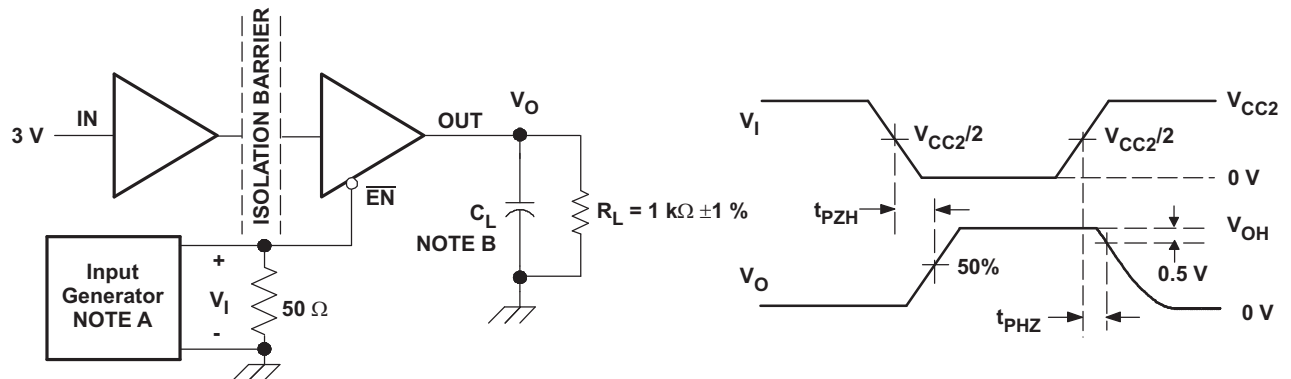


Figure 2. ISO722-Q1 Sleep-Mode High-Level Output Test Circuit and Voltage Waveforms

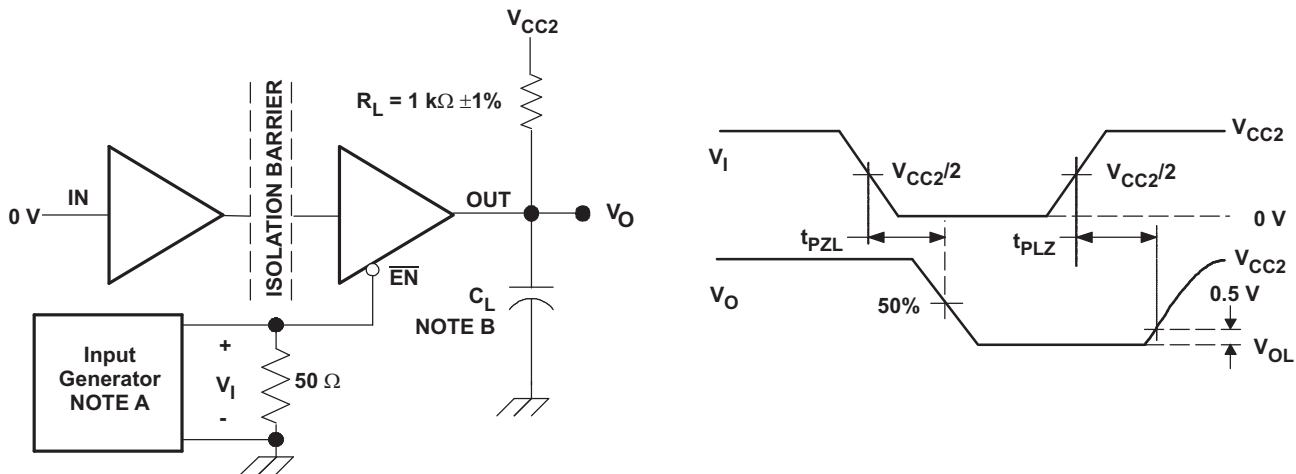
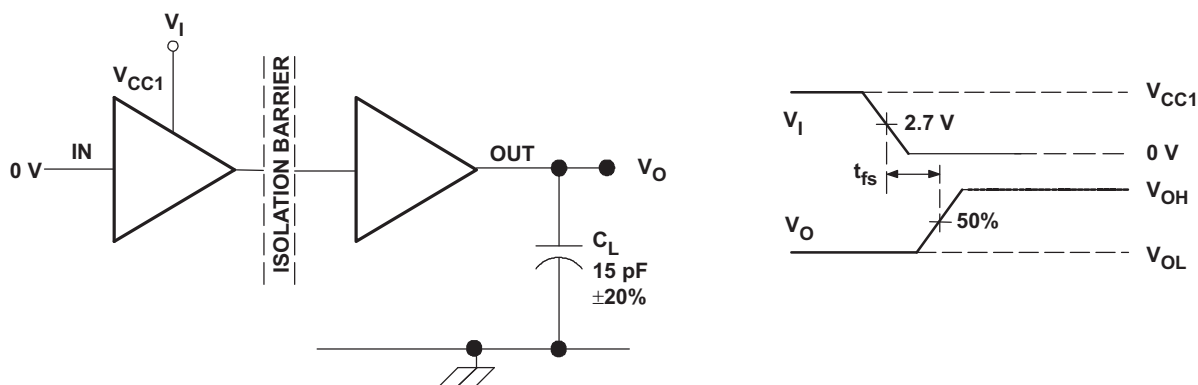


Figure 3. ISO722-Q1 Sleep-Mode Low-Level Output Test Circuit and Voltage Waveforms

NOTE

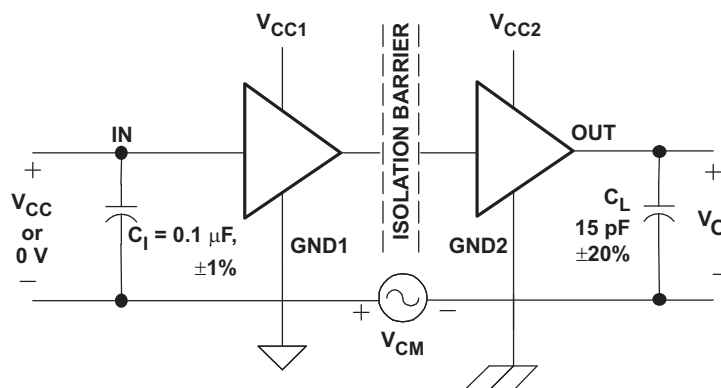
- A: The input pulse is supplied by a generator having the following characteristics:
 PRR ≤ 50 kHz, 50% duty cycle, $t_r \leq 3$ ns, $t_f \leq 3$ ns, $Z_O = 50 \Omega$.
- B: $C_L = 15$ pF ± 20% and includes instrumentation and fixture capacitance.

PARAMETER MEASUREMENT INFORMATION (continued)



NOTE: V_I transition time is 100 ns

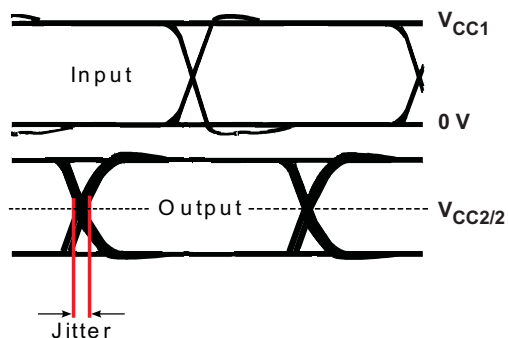
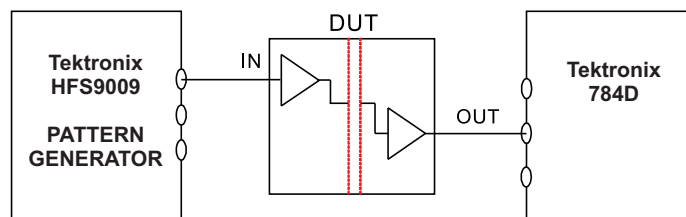
Figure 4. Failsafe Delay Time Test Circuit and Voltage Waveforms



NOTE: Pass/fail criteria is no change in V_O .

Figure 5. Common-Mode Transient Immunity Test Circuit and Voltage Waveform

PARAMETER MEASUREMENT INFORMATION (continued)



NOTE: Bit pattern run length is $2^{16} - 1$. Transition Time is 800 ps. NRZ data input has no more than five consecutive 1s or 0s.

Figure 6. Peak-to-Peak Eye-Pattern Jitter Test Circuit and Voltage Waveform

DEVICE INFORMATION

PACKAGE CHARACTERISTICS

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
L(101)	Minimum air gap (clearance) ⁽¹⁾	Shortest terminal-to-terminal distance through air	4.8			mm
L(102)	Minimum external tracking (creepage)	Shortest terminal to terminal distance across the package surface	4.3			mm
C _{TI}	Tracking resistance (comparative tracking index)	DIN IEC 60112/VDE 0303 Part 1	≥ 175			V
	Minimum internal gap (internal clearance)	Distance through insulation	0.008			mm
R _{IO}	Isolation resistance	Input to output, V _{IO} = 500 V, all pins on each side of the barrier tied together creating a two-terminal device, T _A < 100°C		>10 ¹²		Ω
		Input to output, V _{IO} = 500 V, 100°C ≤ T _A < T _A max.		>10 ¹¹		Ω
C _{IO}	Barrier capacitance, input to output	V _I = 0.4 sin (4E6πt)		1		pF
C _I	Input capacitance to ground	V _I = 0.4 sin (4E6πt)		1		pF

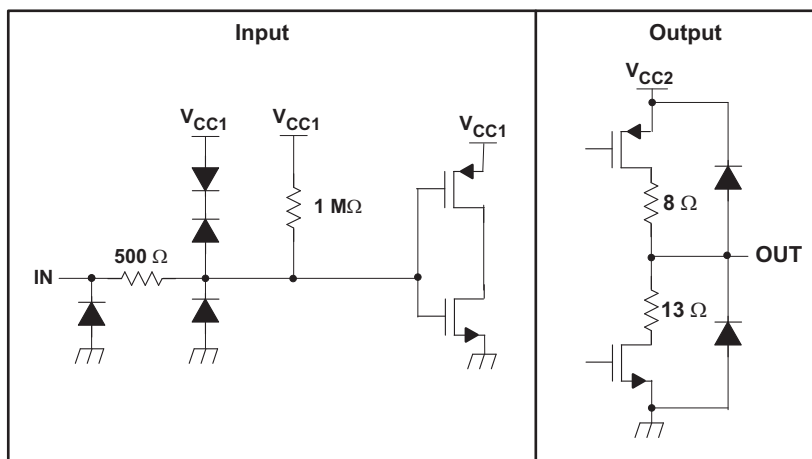
(1) Creepage and clearance requirements are applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed circuit board do not reduce this distance. Creepage and clearance on a printed circuit board become equal according to the measurement techniques shown in the Isolation Glossary. Techniques such as inserting grooves and/or ribs on a printed circuit board are used to help increase these specifications.

IEC 60664-1 RATINGS TABLE

PARAMETER	TEST CONDITIONS	SPECIFICATION
Basic isolation group	Material group	IIIa
Installation classification	Rated mains voltage ≤150 VRMS	I-IV
	Rated mains voltage ≤300 VRMS	I-III

DEVICE I/O SCHEMATIC

Figure 7. Equivalent Input and Output Schematic Diagrams



IEC SAFETY LIMITING VALUES

Safety limiting is designed to prevent potential damage to the isolation barrier upon failure of input or output circuitry. A failure of the IO can allow low resistance to ground or the supply, and without current limiting, dissipate sufficient power to overheat the die and damage the isolation barrier, potentially leading to secondary system failures.

PARAMETER		TEST CONDITIONS	MIN	MAX	UNIT
I _S	Safety input, output, or supply current	$\theta_{JA} = 263^{\circ}\text{C/W}$, $V_I = 5.5\text{ V}$, $T_J = 170^{\circ}\text{C}$, $T_A = 25^{\circ}\text{C}$		100	mA
		$\theta_{JA} = 263^{\circ}\text{C/W}$, $V_I = 3.6\text{ V}$, $T_J = 170^{\circ}\text{C}$, $T_A = 25^{\circ}\text{C}$		153	
T _S	Maximum case temperature			150	°C

The safety-limiting constraint is the absolute maximum junction temperature specified in the absolute maximum ratings table. The power dissipation and junction-to-air thermal impedance of the device installed in the application hardware determines the junction temperature. The junction-to-air thermal resistance in the Thermal Characteristics table is that of a device installed in the JESD51-3, Low Effective Thermal Conductivity Test Board for Leaded Surface Mount Packages and is conservative. The power is the recommended maximum input voltage times the current. The junction temperature is then the ambient temperature plus the power times the junction-to-air thermal resistance.

Table 2. THERMAL CHARACTERISTICS
(over recommended operating conditions unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
θ_{JA}	Junction-to-air thermal resistance	Low-K ⁽¹⁾		263		°C/W
		High-K ⁽¹⁾		125		
θ_{JB}	Junction-to-board thermal resistance			44		°C/W
θ_{JC}	Junction-to-case thermal resistance			75		°C/W
P _D	Device power dissipation	$V_{CC1} = V_{CC2} = 5.5\text{ V}$, $T_J = 150^{\circ}\text{C}$, $C_L = 15\text{ pF}$, Input a 100-Mbps 50% duty cycle square wave			159	mW

(1) Tested in accordance with the Low-K or High-K thermal metric definition of EIA/JESD51-3 for leaded surface-mount packages.

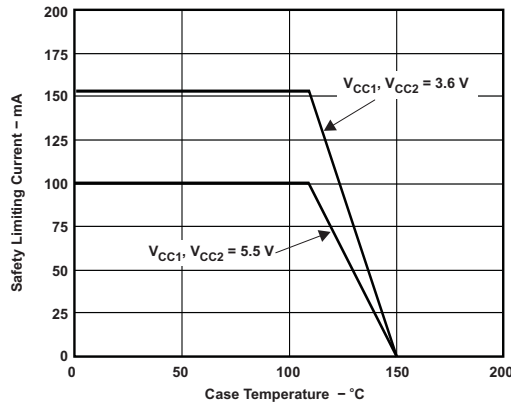


Figure 8. θ_{JC} Thermal Derating Curve Per IEC 60747-5-2

Table 3. FUNCTION TABLE⁽¹⁾

V_{CC1}	V_{CC2}	INPUT (IN)	OUTPUT (OUT)
PU	PU	H	H
		L	L
		Open	H
PD	PU	X	H

(1) PU = powered up ($V_{CC} \geq 3$ V), PD = powered down ($V_{CC} \leq 2.5$ V), X = irrelevant, H = high level, L = low level

TYPICAL CHARACTERISTICS

RMS SUPPLY CURRENT vs SIGNALING RATE

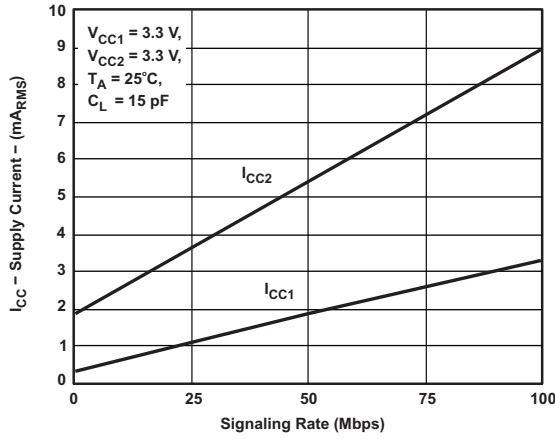


Figure 9.

RMS SUPPLY CURRENT vs SIGNALING RATE

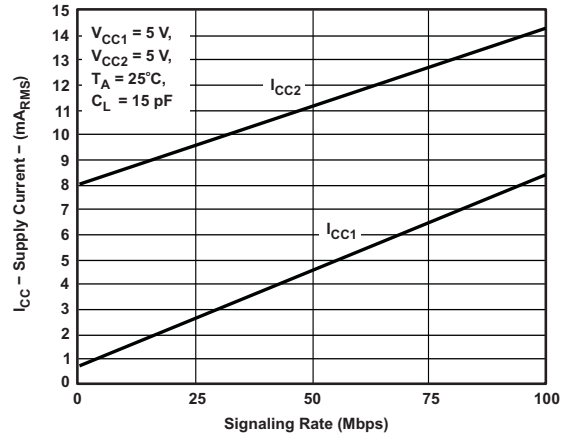


Figure 10.

PROPAGATION DELAY vs FREE-AIR TEMPERATURE

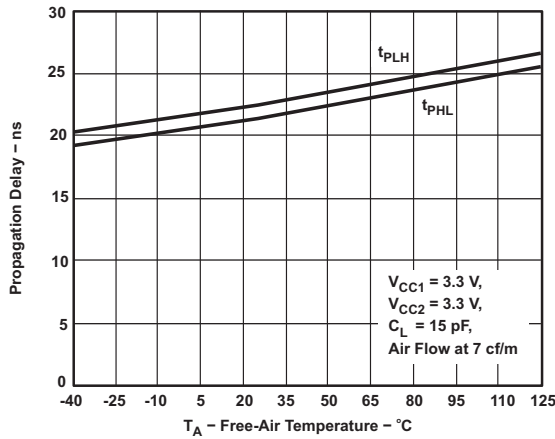


Figure 11.

PROPAGATION DELAY vs FREE-AIR TEMPERATURE

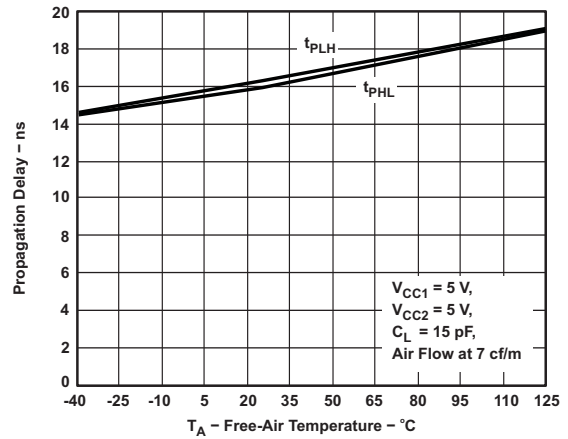


Figure 12.

INPUT THRESHOLD VOLTAGE vs FREE-AIR TEMPERATURE

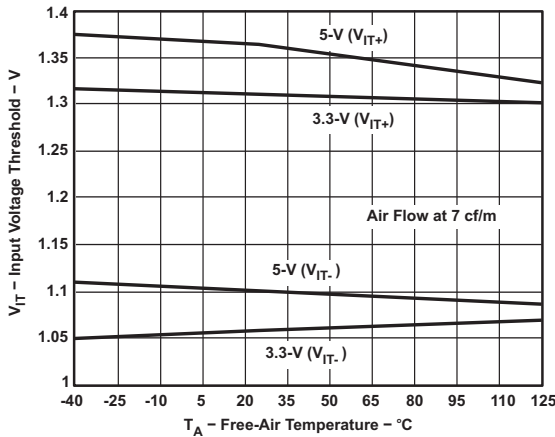


Figure 13.

VCC1 FAILSAFE THRESHOLD VOLTAGE vs FREE-AIR TEMPERATURE

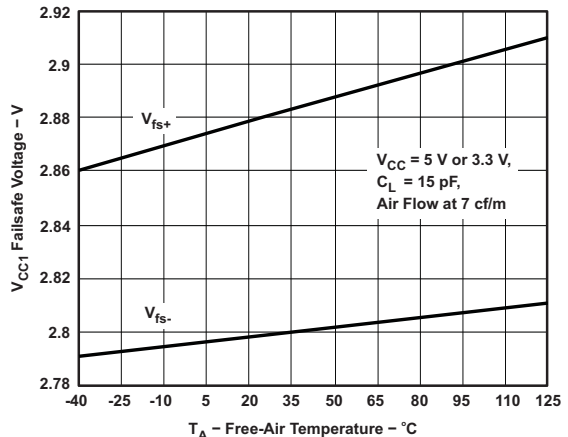


Figure 14.

TYPICAL CHARACTERISTICS (continued)

HIGH-LEVEL OUTPUT CURRENT vs HIGH-LEVEL OUTPUT VOLTAGE

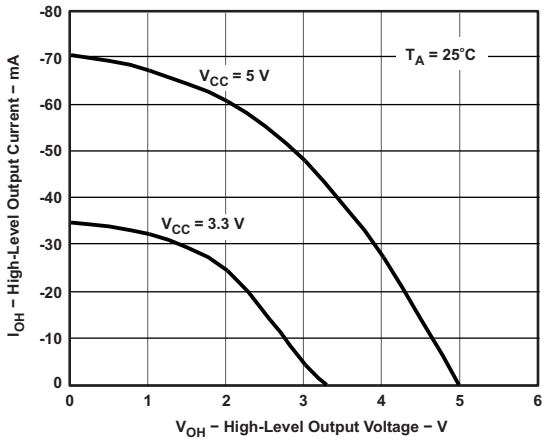


Figure 15.

LOW-LEVEL OUTPUT CURRENT vs LOW-LEVEL OUTPUT VOLTAGE

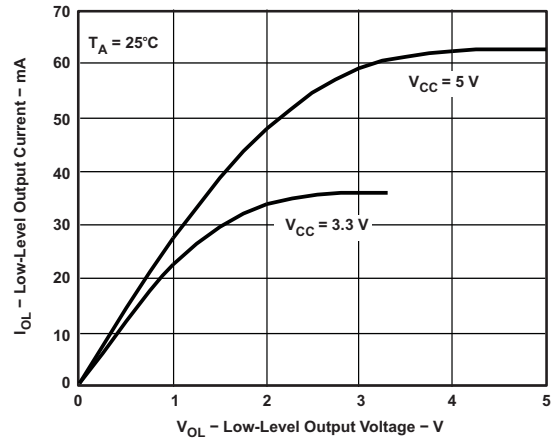


Figure 16.

APPLICATION INFORMATION

MANUFACTURER CROSS-REFERENCE DATA

The ISO72x-Q1 isolator has the same functional pinout as most other vendors, and it is often a pin-for-pin drop-in replacement. The notable differences in the product are propagation delay, signaling rate, power consumption, and transient protection rating. Table 4 is used as a guide for replacing other isolators with the ISO72x-Q1 single-channel isolators.

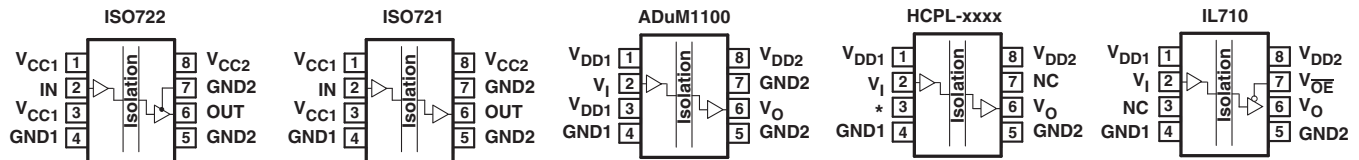


Figure 17. Pinout Cross Reference

Table 4. Competitive Cross Reference

ISOLATOR	PIN 1	PIN 2	PIN 3	PIN 4	PIN 5	PIN 6	PIN 7		PIN 8
							ISO721	ISO722	
ISO721 ^{(1) (2)}	V _{CC1}	IN	V _{CC1}	GND1	GND2	OUT	GND2	$\overline{\text{EN}}$	V _{CC2}
ADuM1100 ^{(1) (2)}	V _{DD1}	V _I	V _{DD1}	GND1	GND2	V _O	GND2		V _{DD2}
HCPL-xxxx	V _{DD1}	V _I	Leave Open ⁽³⁾	GND1	GND2	V _O	NC ⁽⁴⁾		V _{DD2}
IL710	V _{DD1}	V _I	NC ⁽⁵⁾	GND1	GND2	V _O	V $\overline{\text{OE}}$		V _{DD2}

- (1) The ISO721 pin 1 and pin 3 are internally connected together. Either or both may be used as V_{CC1}.
- (2) The ISO721 pin 5 and pin 7 are internally connected together. Either or both may be used as GND2.
- (3) Pin 3 of the HCPL devices must be left open. This is not a problem when substituting an ISO721, because the extra V_{CC1} on pin 3 may be left open circuit as well.
- (4) An HCPL device pin 7 must be left floating (open) or grounded when an ISO722 device is to be used as a drop-in replacement. If pin 7 of the ISO722 device is placed in a high logic state, the output of the device is disabled.
- (5) Pin 3 of the IL710 must not be tied to ground on the circuit board, because this shorts the ISO721 V_{CC1} to ground. The IL710 pin 3 may only be tied to V_{CC} or left open to drop in an ISO721.

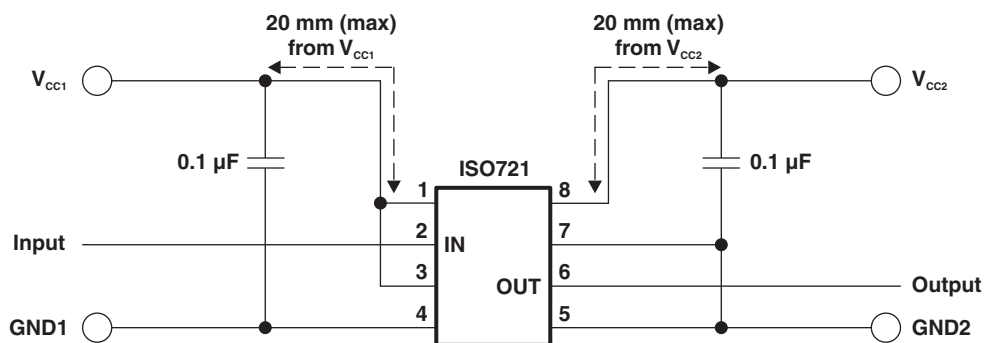
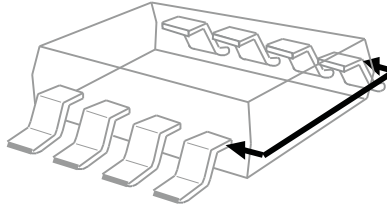


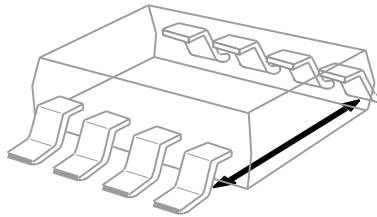
Figure 18. Basic Application Circuit

ISOLATION GLOSSARY

Creepage Distance — The shortest path between two conductive input to output leads measured along the surface of the insulation. The shortest distance path is found around the end of the package body.



Clearance — The shortest distance between two conductive input to output leads measured through air (line of sight).



Input-to-Output Barrier Capacitance — The total capacitance between all input terminals connected together, and all output terminals connected together.

Input-to-Output Barrier Resistance — The total resistance between all input terminals connected together, and all output terminals connected together.

Primary Circuit — An internal circuit directly connected to an external supply mains or other equivalent source which supplies the primary circuit electric power.

Secondary Circuit — A circuit with no direct connection to primary power, and derives its power from a separate isolated source.

Comparative Tracking Index (CTI) — CTI is an index used for electrical insulating materials and is defined as the numerical value of the voltage that causes failure by tracking during standard testing. Tracking is the process that produces a partially conducting path of localized deterioration on or through the surface of an insulating material as a result of the action of electric discharges on or close to an insulation surface -- the higher CTI value of the insulating material, the smaller the minimum creepage distance.

Generally, insulation breakdown occurs either through the material, over its surface, or both. Surface failure may arise from flashover or from the progressive degradation of the insulation surface by small localized sparks. Such sparks are the result of the breaking of a surface film of conducting contaminant on the insulation. The resulting break in the leakage current produces an overvoltage at the site of the discontinuity, and an electric spark is generated. These sparks often cause carbonization on insulation material and lead to a carbon track between points of different potential. This process is known as *tracking*.

Insulation

Operational insulation — Insulation needed for the correct operation of the equipment

Basic insulation — Insulation to provide basic protection against electric shock

Supplementary insulation — Independent insulation applied in addition to basic insulation in order to ensure protection against electric shock in the event of a failure of the basic insulation

Double insulation — Insulation comprising both basic and supplementary insulation

Reinforced insulation — A single insulation system that provides a degree of protection against electric shock equivalent to double insulation

Pollution Degree

Pollution Degree 1 — No pollution, or only dry, nonconductive pollution occurs. The pollution has no influence.

Pollution Degree 2 — Normally, only nonconductive pollution occurs. However, a temporary conductivity caused by condensation must be expected.

Pollution Degree 3 — Conductive pollution occurs or dry nonconductive pollution occurs that becomes conductive due to condensation, which is to be expected.

Pollution Degree 4 — Continuous conductivity occurs due to conductive dust, rain, or other wet conditions.

Installation Category

Overvoltage Category — This section addresses insulation coordination by identifying the transient overvoltages that may occur and by assigning four different levels as indicated in IEC 60664.

I: Signal Level — Special equipment or parts of equipment

II: Local Level — Portable equipment, etc.

III: Distribution Level — Fixed installation

IV: Primary Supply Level — Overhead lines, cable systems

Each category should be subject to smaller transients than the category above.

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISO721QDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO722QDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISO721QDRQ1	SOIC	D	8	2500	367.0	367.0	35.0
ISO722QDRQ1	SOIC	D	8	2500	367.0	367.0	35.0

D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).
 B. This drawing is subject to change without notice.
 C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
 D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
 E. Reference JEDEC MS-012 variation AA.

D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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